

/ Descriptions

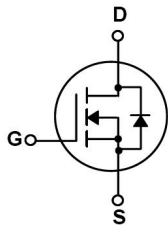
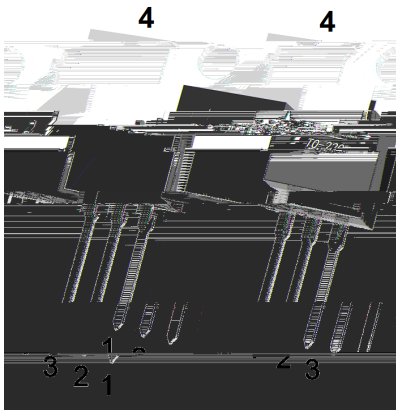
TO-220 N MOS
N-CHANNEL MOSFET in a TO-220 Plastic Package.

/ Features

Low gate charge, low crss, fast switching, HF Product.

DC/DC

These devices are well suited for high efficiency switching DC/DC converters, and switch mode power supplies.



PIN1 G PIN 2 4 D PIN 3 S

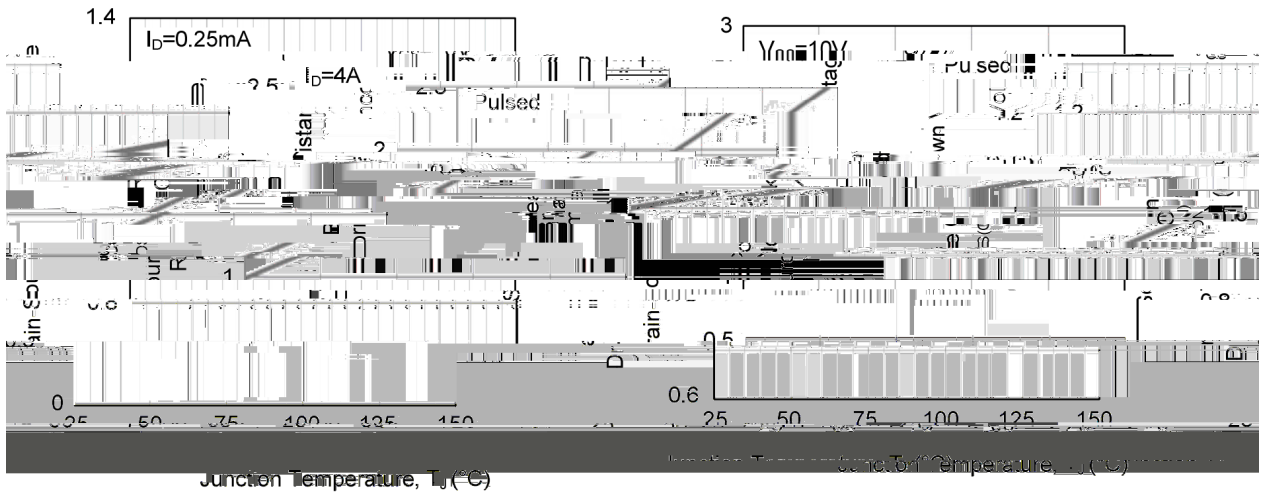
/ Marking

See Marking Instructions.

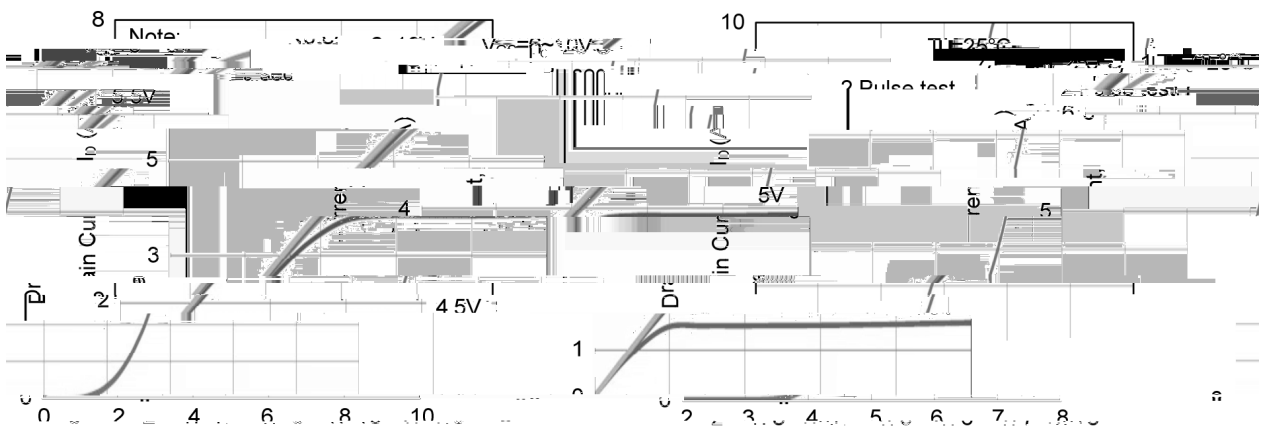
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	650	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	8	A
Drain Current - Pulsed	I_{DM}	32	A
Gate-Source Voltage	V_{GS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	597	mJ
Avalanche Current	I_{AR}	10.5	A
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	110	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	
Thermal resistance, junction- case	$R_{\theta JC}$	1.14	/W

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0V$ $I_D=250\mu A$	650	700		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=650V$ $V_{GS}=0V$			1.0	μA
Gate-Body Leakage Current, Forward	I_{GSS}	$V_{GS}=10V$ $T_J=55^\circ\text{C}$ $T_J=150^\circ\text{C}$	10.4955	354.5	9395.7803	Tm1.4429 T5(GS)Tj.48 .0005 Tc1.

/ Electrical Characteristic Curve



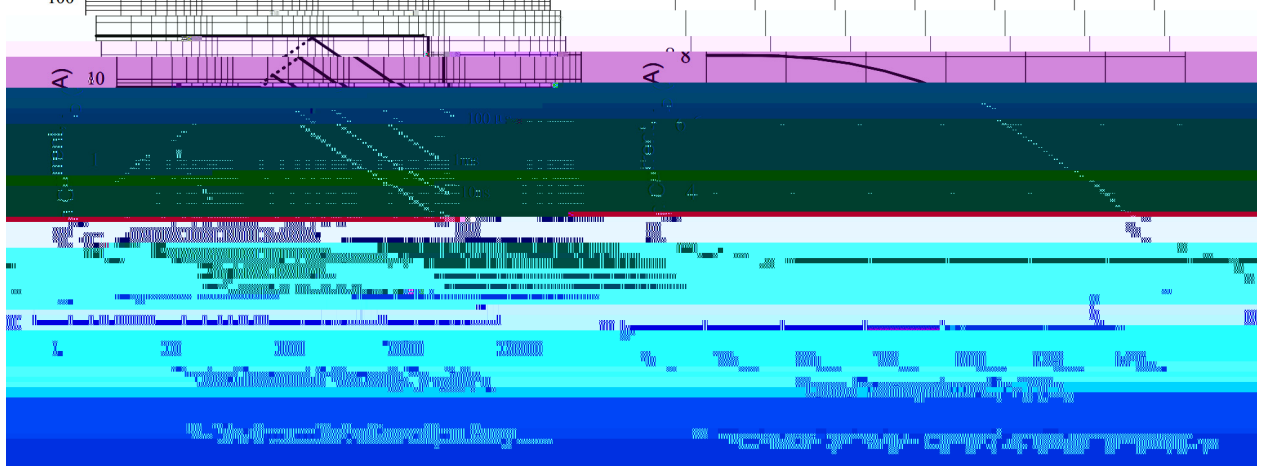
1 Breakdown Voltage vs. Junction Temperature



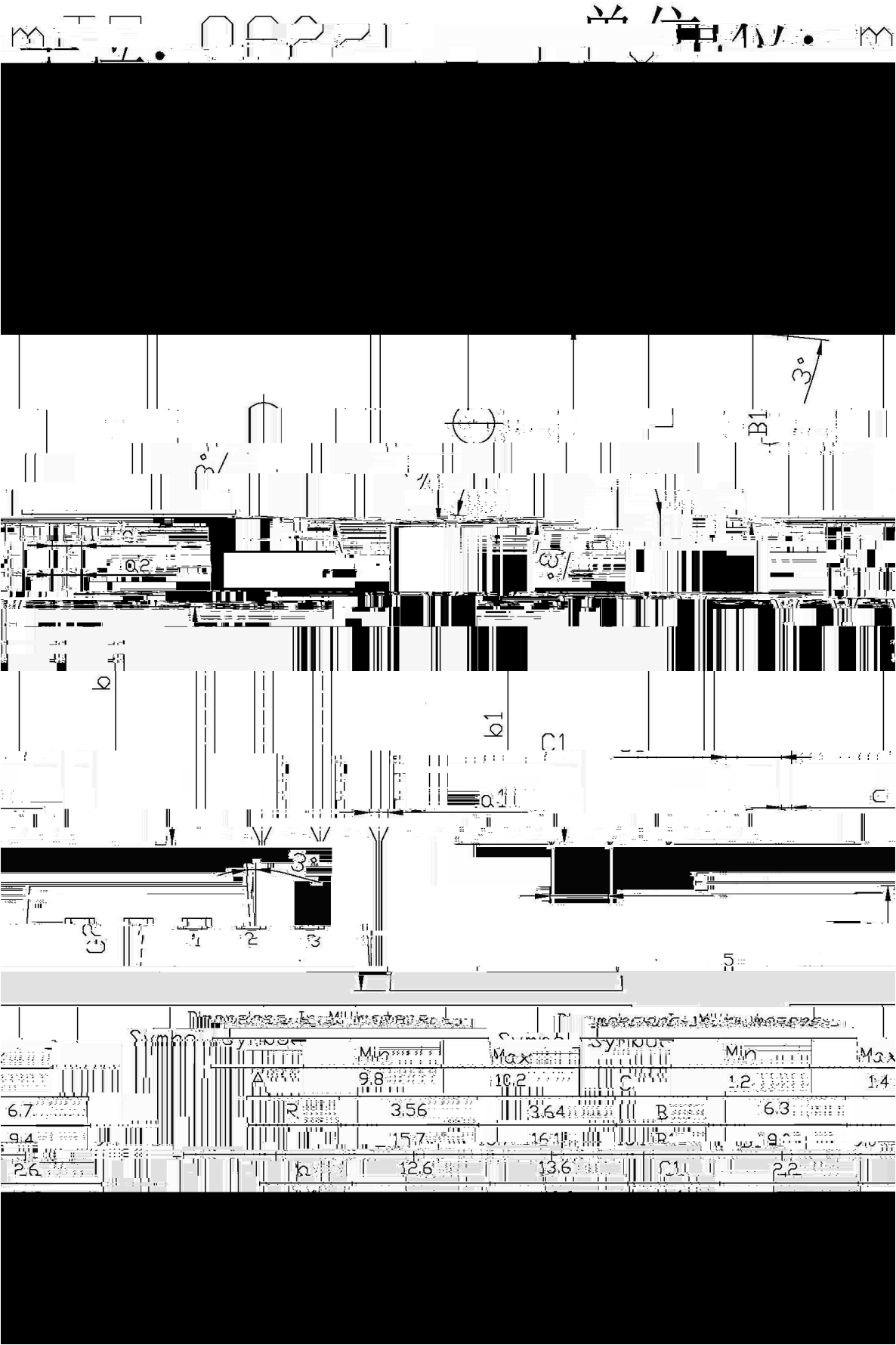
2 Drain-Source On-Resistance vs. Drain-Source Voltage



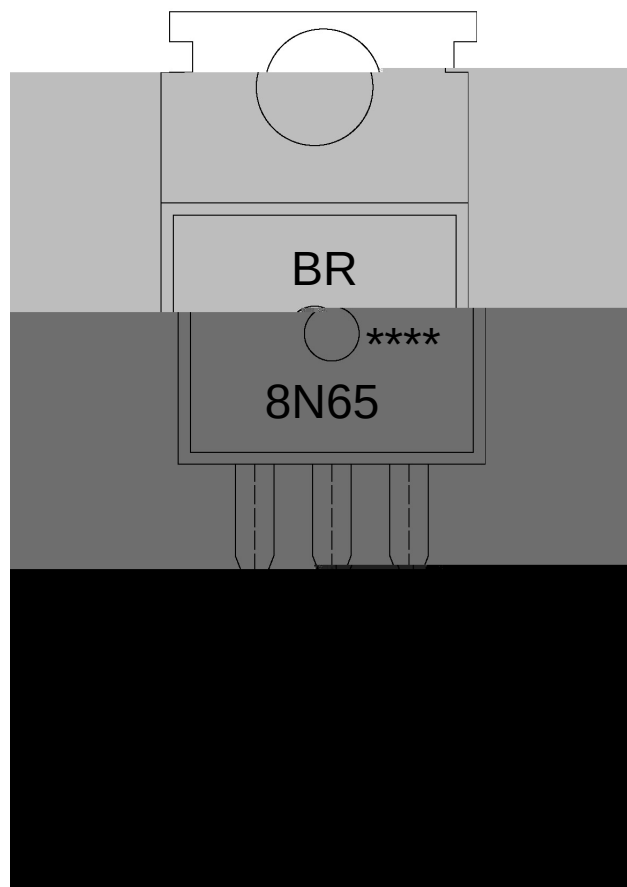
3 Drain Current vs. Drain-Source Voltage



/ Package Dimensions



/ Marking Instructions



BR

8N65

Note:

BR: Company Code

8N65: Product Type Code

*****: Lot No. Code, code change with Lot No

() / Temperature Profile for Dip Soldering(Pb-Free)
